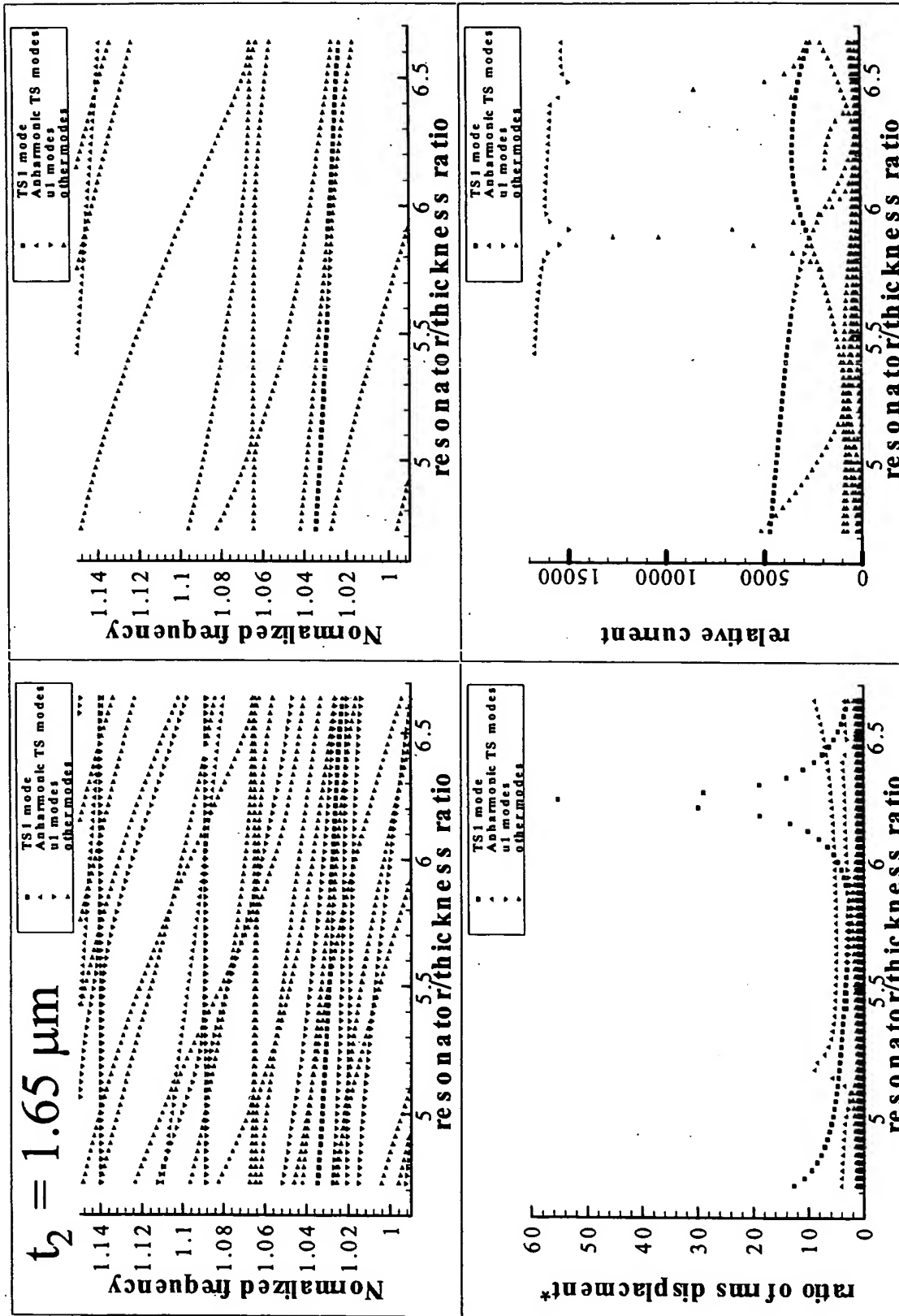


1A

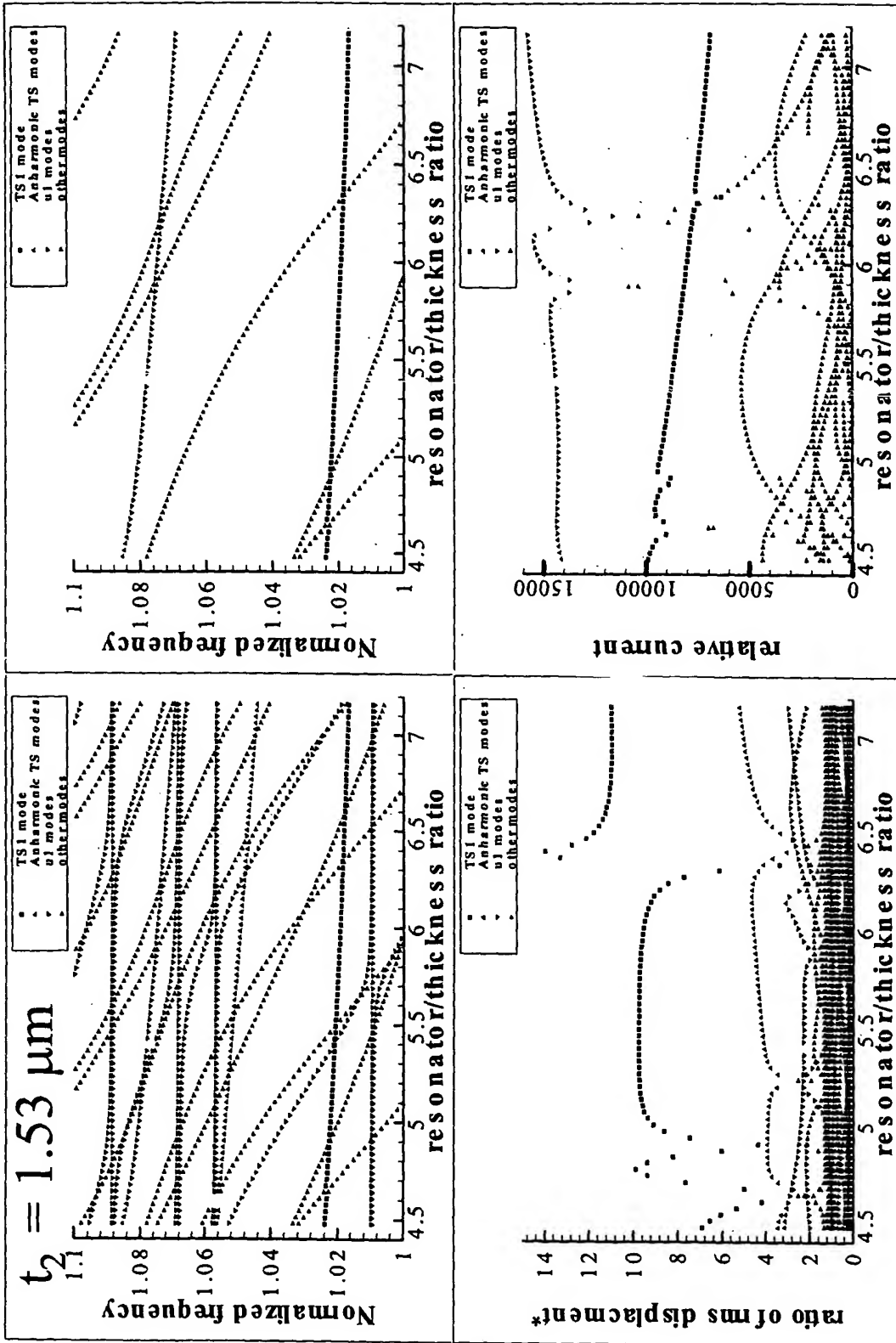


1D

FIG'S 1A-1D

1C

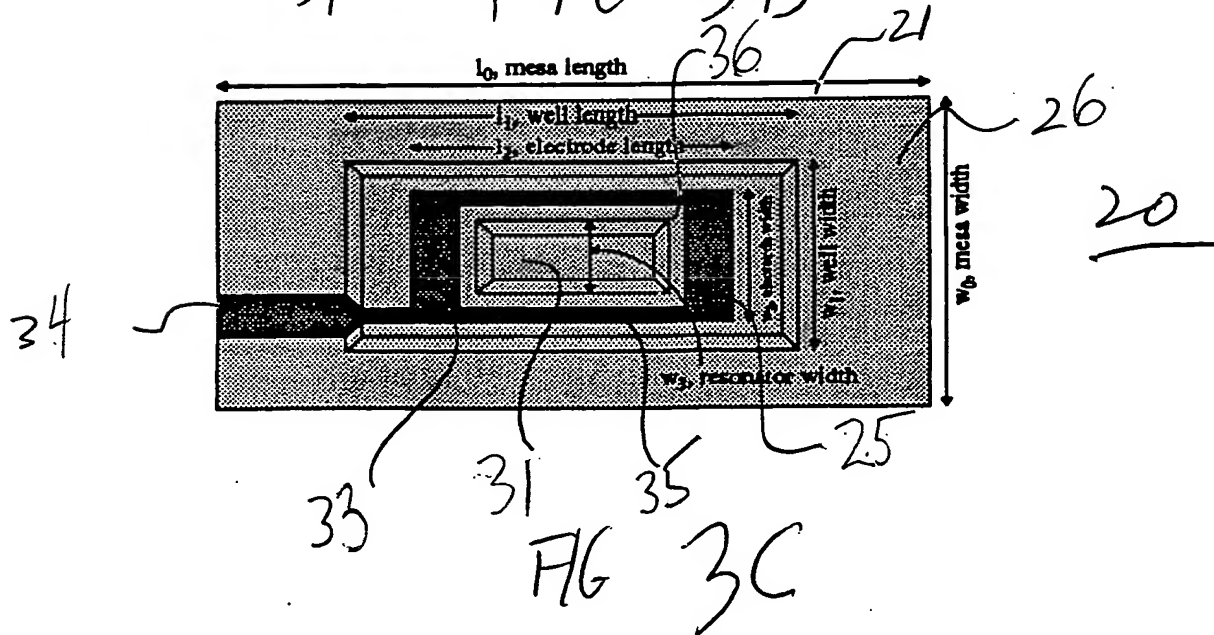
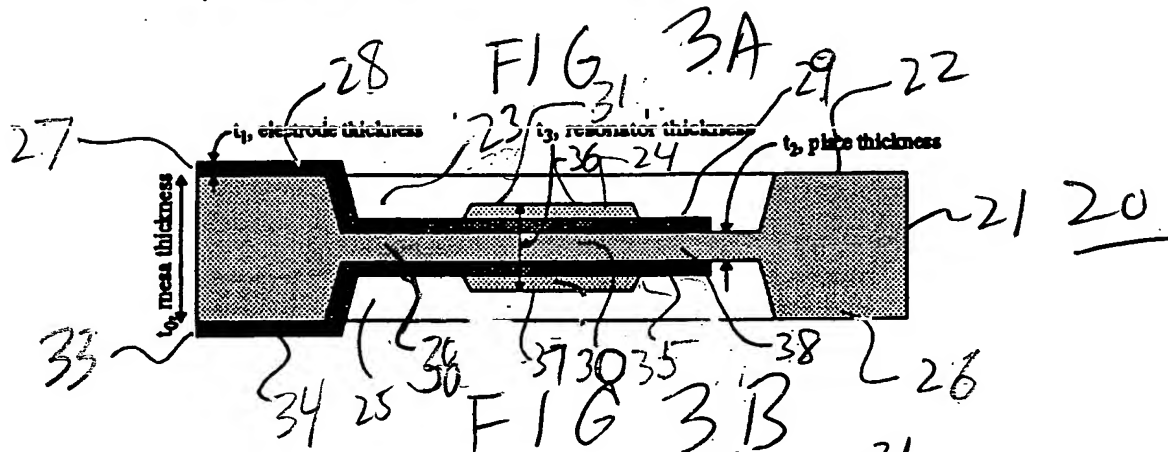
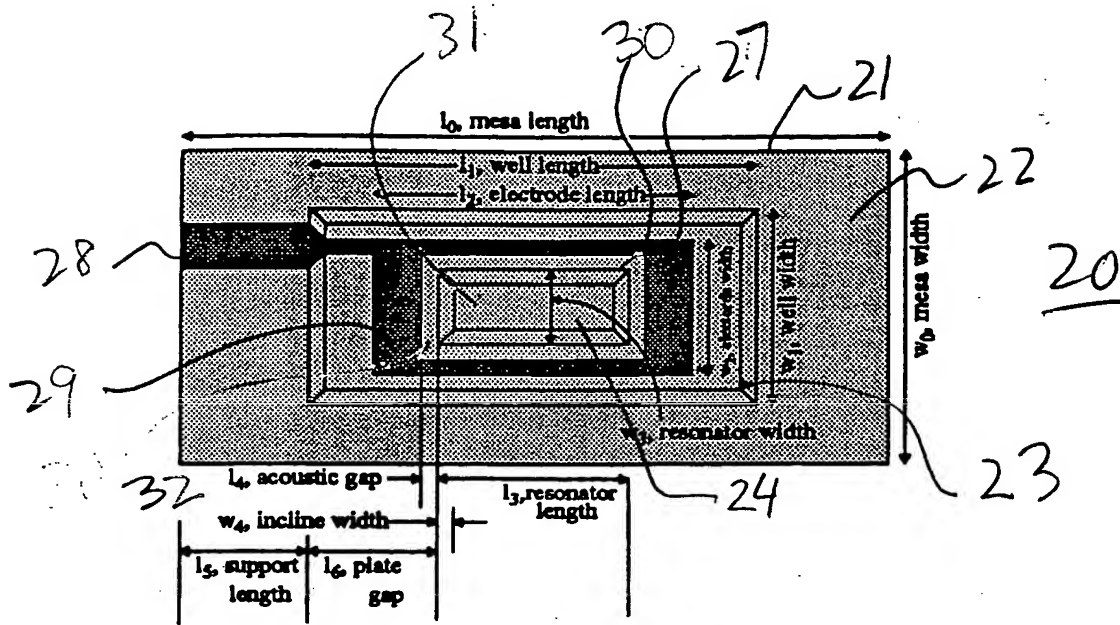
2A



2B

FIGS 2A-2D

2C



40



FIG. 4C

A cross-sectional view of a semiconductor device. The device consists of a central rectangular region (52) surrounded by a well (55). The well is further surrounded by a mesa (54). The dimensions are labeled as follows:

- l_0 , mesa length
- l_1 , well length
- l_2 , electrode length
- w_1 , well width
- w_0 , mesa width

40

FIG. 5A

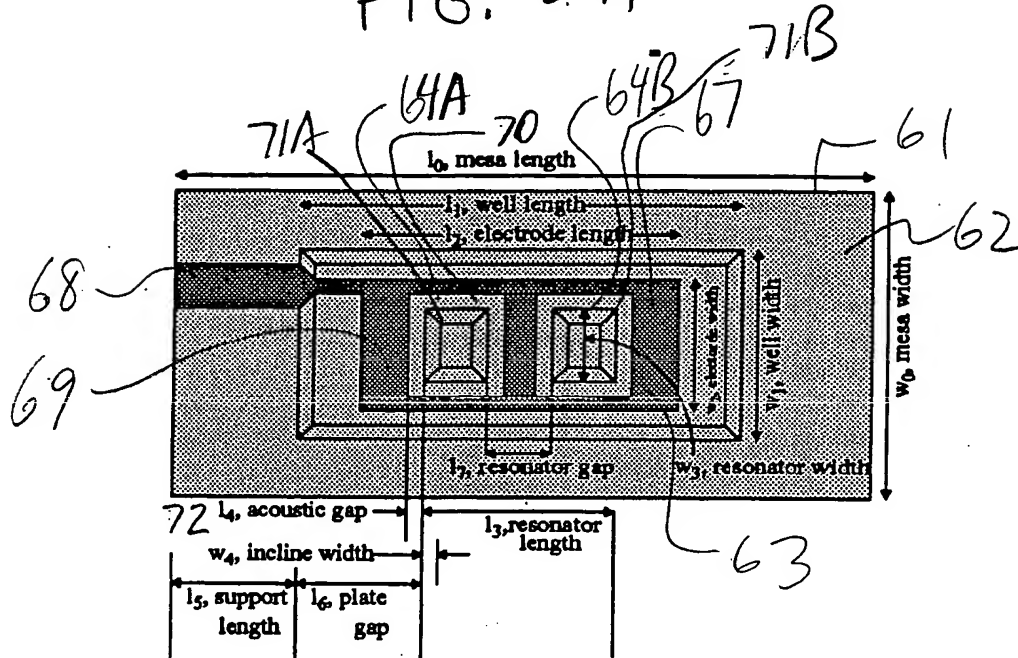


FIG. 5B

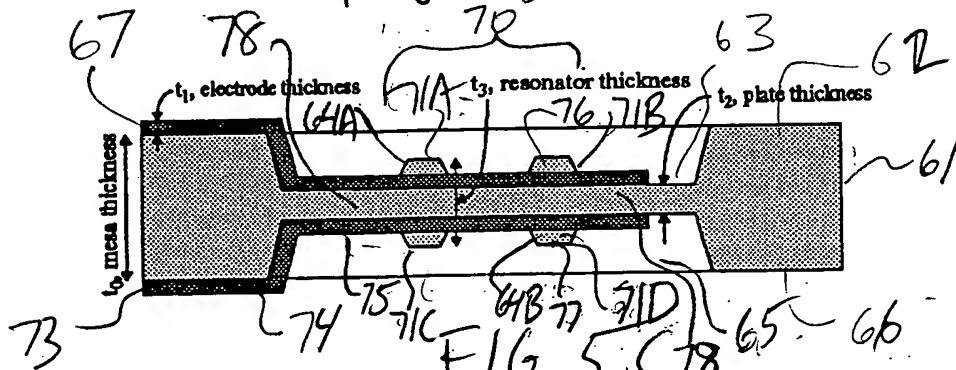
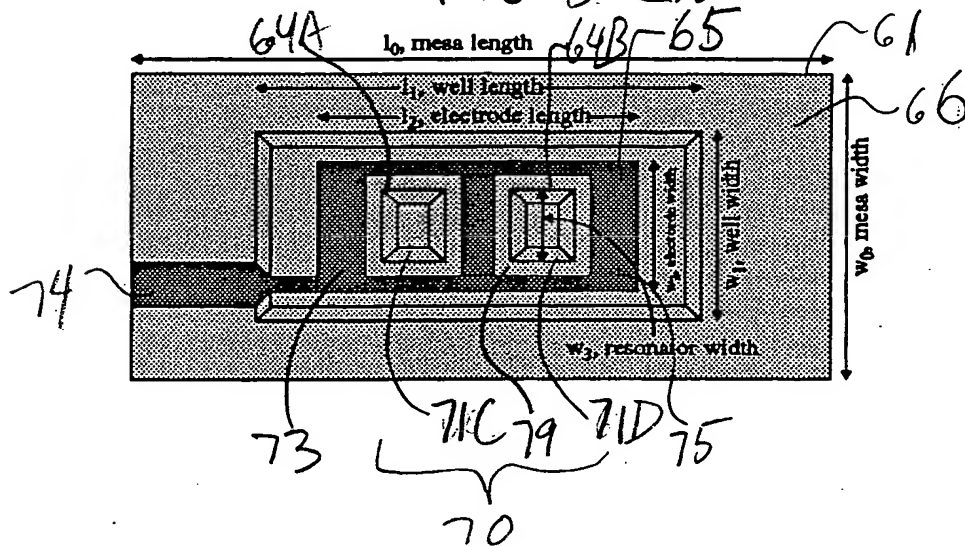
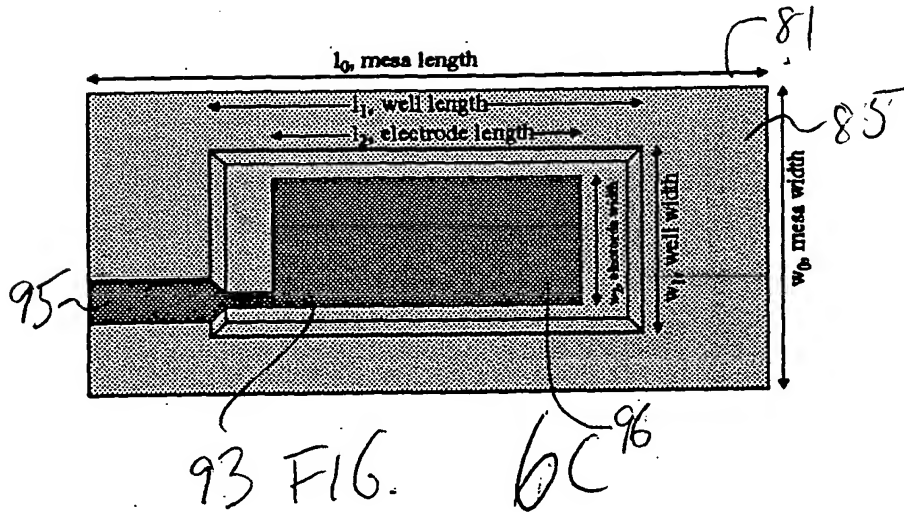
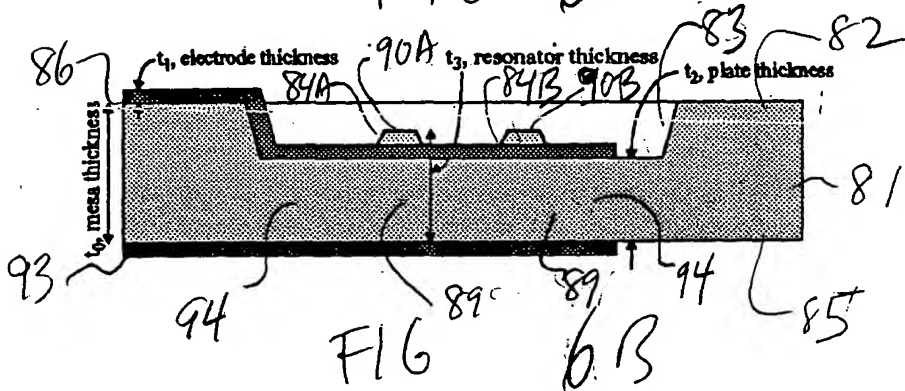
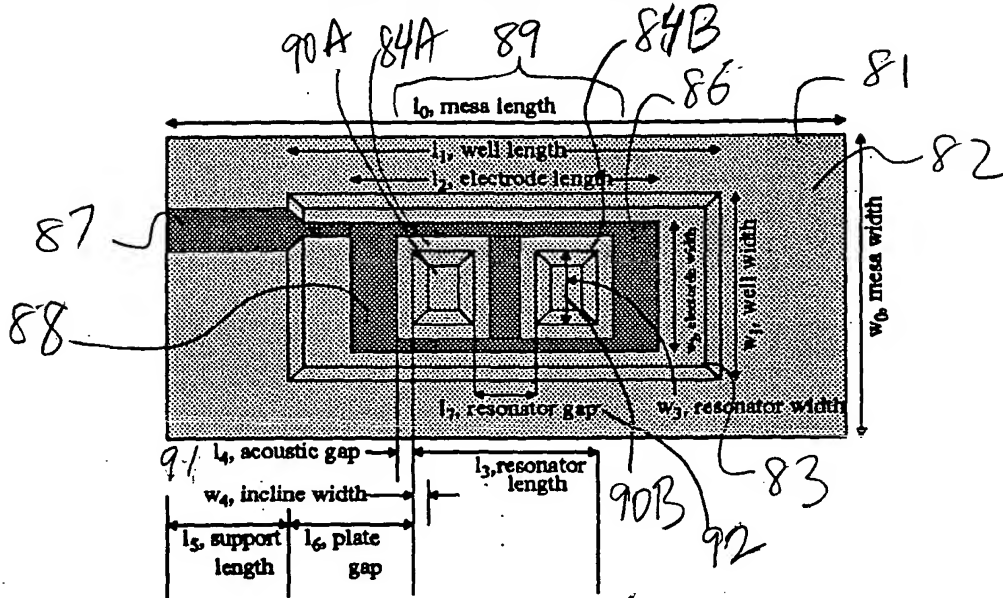
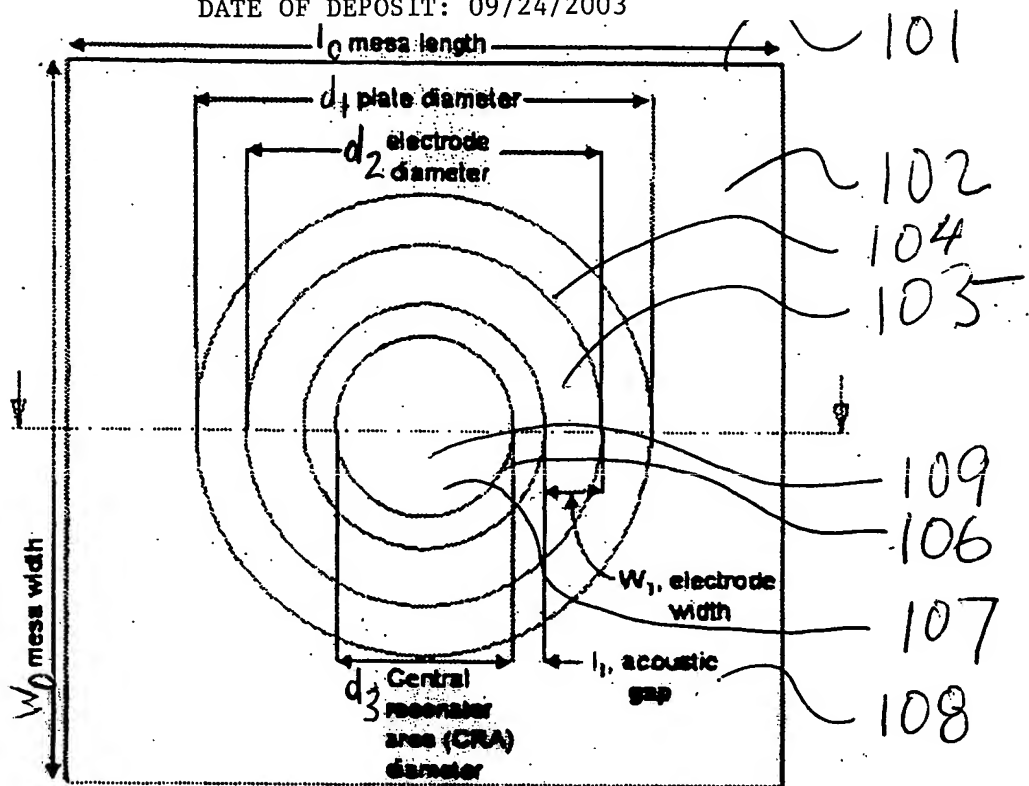


FIG. 5C







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FIG. 7A

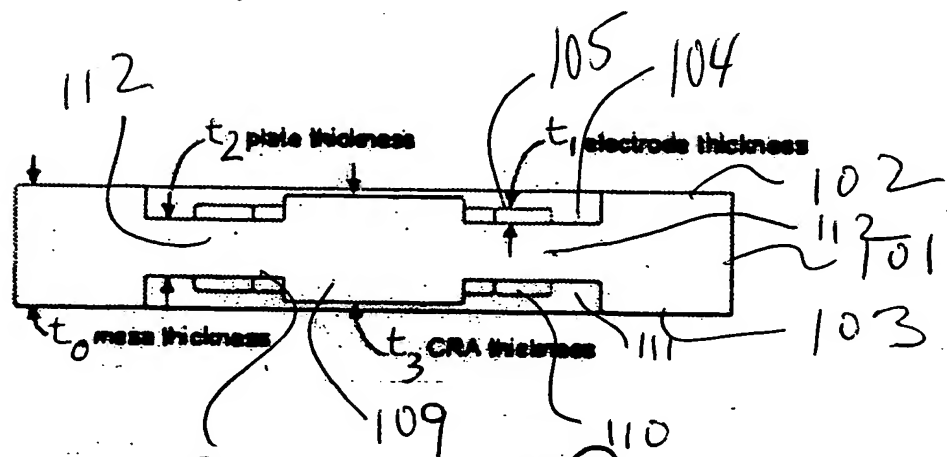


FIG. 7B